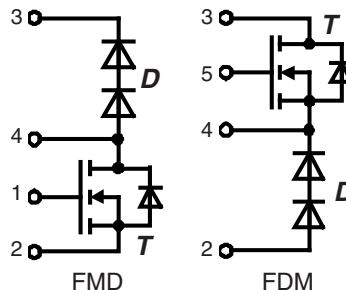


CoolMOS™ 1) Power MOSFET

with HiPerDyn™ FRED

Buck and Boost Topologies

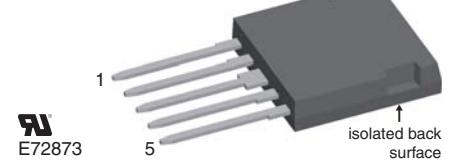
Electrically isolated back surface
 2500 V electrical isolation
 N-Channel Enhancement Mode
 Low $R_{DS(on)}$, high V_{DSS} MOSFET
 Ultra low gate charge



$$I_{D25} = 15 \text{ A}$$

$$V_{DSS} = 600 \text{ V}$$

$$R_{DS(on) \text{ max}} = 0.165 \Omega$$

ISOPLUS i4™

Features

- Silicon chip on Direct-Copper-Bond substrate
 - high power dissipation
 - isolated mounting surface
 - 2500 V electrical isolation
 - low drain to tab capacitance (< 40 pF)
- Fast CoolMOS™ 1) power MOSFET 4th generation
 - high blocking capability
 - lowest resistance
 - avalanche rated for unclamped inductive switching (UIS)
 - low thermal resistance due to reduced chip thickness
- Enhanced total power density
- HiPerDyn™ FRED
 - consisting of series connected diodes
 - enhanced dynamic behaviour for high frequency operation

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)

Advantages

- Easy assembly: no screws or isolation foils required
- Space savings
- High power density
- High reliability

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

MOSFET T			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	15	A
I_{D90}	$T_C = 90^\circ\text{C}$	11	A
E_{AS} E_{AR}	single pulse repetitive } $I_D = 7.9 \text{ A}; T_C = 25^\circ\text{C}$	522 0.79	mJ mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480 \text{ V}$	50	V/ns

Symbol	Conditions	Characteristic Values			
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}$		150	165	m Ω
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 0.79 \text{ mA}$	2.5	3	3.5	V
I_{DSS}	$V_{DS} = 600 \text{ V}; V_{GS} = 0 \text{ V}$			1	μA
				10	μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			100	nA
C_{iss} C_{oss}	$V_{GS} = 0 \text{ V}; V_{DS} = 100 \text{ V}$ $f = 1 \text{ MHz}$		2000 100		pF pF
Q_g Q_{gs} Q_{gd}	$V_{GS} = 0 \text{ to } 10 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 12 \text{ A}$		40 9 13	52	nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off} $E_{rec off}$	$V_{GS} = 10 \text{ V}; V_{DS} = 400 \text{ V}$ $I_D = 12 \text{ A}; R_G = 3.3 \Omega$		12 5 50 5 tbd tbd tbd		ns ns ns ns mJ mJ mJ
R_{thJC} R_{thCH}	with heat transfer paste		0.35	1.1	K/W K/W

MOSFET T Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)					
I_S	$V_{GS} = 0\text{ V}$			12	A
V_{SD}	$I_F = 12\text{ A}; V_{GS} = 0\text{ V}$		0.9	1.2	V
t_{rr}	$I_F = 12\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 400\text{ V}$		390		ns
Q_{RM}			7.5		μC
I_{RM}			38		A

Diode D (data for series connection)

Symbol	Conditions	Maximum Ratings	
V_{RRM}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
I_{F25}	$T_C = 25^{\circ}\text{C}$	15	A
I_{F90}	$T_C = 90^{\circ}\text{C}$	8	A

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	$I_F = 15\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		2.50	V
				3.00	V
	$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$		2.00	A
				2.55	A
I_R	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		1	μA
		$T_{VJ} = 150^{\circ}\text{C}$		0.08	mA
I_{FSM}	$t = 10\text{ ms (50 Hz), sine};$	$T_{VJ} = 45^{\circ}\text{C}$		150	A
I_{RM}	$I_F = 20\text{ A}; V_R = 100\text{ V};$ $-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		3	A
t_{rr}				35	ns
R_{thJC}	with heat transfer paste			2.4	K/W
R_{thJH}		0.8			K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-55...+150	$^{\circ}\text{C}$
T_{stg}	storage	-55...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} < 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
C_P	coupling capacity between shorted pins and mounting tab in the case		40		pF
d_S, d_A	pin - pin	1.7			mm
d_S, d_A	pin - backside metal	5.5			mm
Weight			9		g

ISOPLUS i4™ Outline

